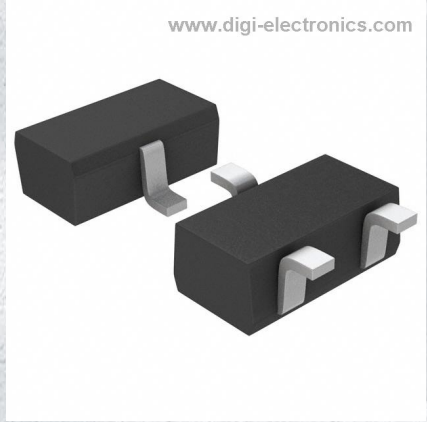
UNR9215J0L Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	UNR9215J0L-DG
Manufacturer	Panasonic Electronic Components
Manufacturer Product Number	UNR9215J0L
Description	TRANS PREBIAS NPN 50V SSMINI3
Detailed Description	Pre-Biased Bipolar Transistor (BJT) NPN - Pre-Biased 50 V 100 mA 150 MHz 125 mW Surface Mount SSMini3-F1

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
UNR9215J0L	Panasonic Electronic Components
Series:	Product Status:
-	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN - Pre-Biased	100 mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50 V	10 kOhms
DC Current Gain (hFE) (Min) @ Ic, Vce:	Vce Saturation (Max) @ Ib, Ic:
160 @ 5mA, 10V	250mV @ 300µA, 10mA
Current - Collector Cutoff (Max):	Frequency - Transition:
500nA	150 MHz
Power - Max:	Mounting Type:
125 mW	Surface Mount
Package / Case:	Supplier Device Package:
SC-89, SOT-490	SSMini3-F1
Base Product Number:	
UNR9215	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	ECCN:
1 (Unlimited)	EAR99
HTSUS:	
8541.21.0075	

UNR921xJ Series (UN921xJ Series)

Silicon NPN epitaxial planar type

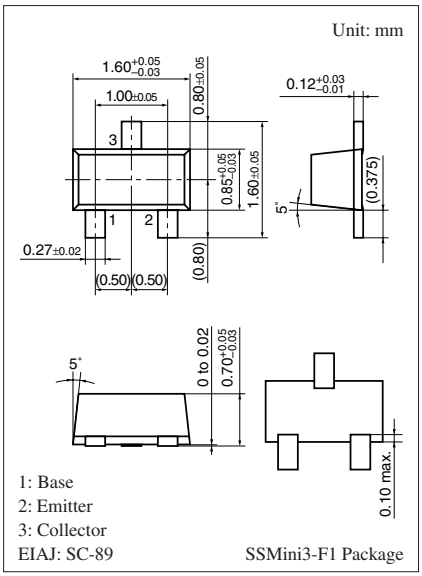
For digital circuits

■ Features

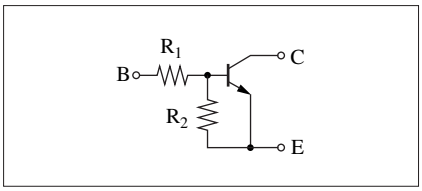
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- SS-Mini type package, allowing automatic insertion through tape packing.

■ Resistance by Part Number

	Marking Symbol	(R_1)	(R_2)
• UNR9210J (UN9210J)	8L	47 kΩ	—
• UNR9211J (UN9211J)	8A	10 kΩ	10 kΩ
• UNR9212J (UN9212J)	8B	22 kΩ	22 kΩ
• UNR9213J (UN9213J)	8C	47 kΩ	47 kΩ
• UNR9214J (UN9214J)	8D	10 kΩ	47 kΩ
• UNR9215J (UN9215J)	8E	10 kΩ	—
• UNR9216J (UN9216J)	8F	4.7 kΩ	—
• UNR9217J (UN9217J)	8H	22 kΩ	—
• UNR9218J (UN9218J)	8I	0.51 kΩ	5.1 kΩ
• UNR9219J (UN9219J)	8K	1 kΩ	10 kΩ
• UNR921AJ	8X	100 kΩ	100 kΩ
• UNR921BJ	8Y	100 kΩ	—
• UNR921CJ	8Z	—	47 kΩ
• UNR921DJ (UN921DJ)	8M	47 kΩ	10 kΩ
• UNR921EJ (UN921EJ)	8N	47 kΩ	22 kΩ
• UNR921FJ (UN921FJ)	8O	4.7 kΩ	10 kΩ
• UNR921KJ (UN921KJ)	8P	10 kΩ	4.7 kΩ
• UNR921LJ (UN921LJ)	8Q	4.7 kΩ	4.7 kΩ
• UNR921MJ	EL	2.2 kΩ	47 kΩ
• UNR921NJ	EX	4.7 kΩ	47 kΩ
• UNR921TJ (UN921TJ)	EZ	22 kΩ	47 kΩ
• UNR921VJ	FD	2.2 kΩ	2.2 kΩ



Internal Connection



■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	50	V
Collector-emitter voltage (Base open)	V_{CEO}	50	V
Collector current	I_C	100	mA
Total power dissipation	P_T	125	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−55 to +125	°C

Note) The part numbers in the parenthesis show conventional part number.

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)		V_{CBO}	$I_C = 10\ \mu A$, $I_E = 0$	50			V
Collector-emitter voltage (Base open)		V_{CEO}	$I_C = 2$ mA, $I_B = 0$	50			V
Collector-base cut-off current (Emitter open)		I_{CBO}	$V_{CB} = 50$ V, $I_E = 0$			0.1	μA
Collector-emitter cut-off current (Base open)		I_{CEO}	$V_{CE} = 50$ V, $I_B = 0$			0.5	μA
Emitter-base cut-off current (Collector open)	UNR9210J/9215J/9216J/9217J/921BJ	I_{EBO}	$V_{EB} = 6$ V, $I_C = 0$			0.01	mA
	UNR9213J/921AJ					0.1	
	UNR9212J/9214J/921DJ/921EJ/921MJ/921NJ/921TJ					0.2	
	UNR9211J					0.5	
	UNR921FJ/921KJ					1.0	
	UNR9219J					1.5	
	UNR9218J/921CJ/921LJ/921VJ					2.0	
Forward current transfer ratio	UNR921VJ	h_{FE}	$V_{CE} = 10$ V, $I_C = 5$ mA	6		20	—
	UNR9218J/921KJ/921LJ			20			
	UNR9219J/921DJ/921FJ			30			
	UNR9211J			35			
	UNR9212J/921EJ			60			
	UNR9213J/9214J/921AJ/921CJ/921MJ			80			
	UNR921NJ/921TJ			80		400	
	UNR9210J/9215J/9216J/9217J/921BJ			160		460	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 10$ mA, $I_B = 0.3$ mA			0.25	V
Output voltage high-level		V_{OH}	$V_{CC} = 5$ V, $V_B = 0.5$ V, $R_L = 1$ kΩ	4.9			V
Output voltage low-level		V_{OL}	$V_{CC} = 5$ V, $V_B = 2.5$ V, $R_L = 1$ kΩ			0.2	V
	UNR9213J/921BJ/921KJ		$V_{CC} = 5$ V, $V_B = 3.5$ V, $R_L = 1$ kΩ				
	UNR921DJ		$V_{CC} = 5$ V, $V_B = 10$ V, $R_L = 1$ kΩ				
	UNR921EJ		$V_{CC} = 5$ V, $V_B = 6$ V, $R_L = 1$ kΩ				
	UNR921AJ		$V_{CC} = 5$ V, $V_B = 5$ V, $R_L = 1$ kΩ				
Transition frequency		f_T	$V_{CB} = 10$ V, $I_E = -2$ mA, f = 200 MHz		150		MHz
Input resistance	UNR9218J	R_1		−30%	0.51	+30%	kΩ
	UNR9219J				1		
	UNR921MJ/921VJ				2.2		
	UNR9216J/921FJ/921LJ/921NJ				4.7		
	UNR9211J/9214J/9215J/921KJ				10		
	UNR9212J/9217J/921TJ				22		
	UNR9210J/9213J/921DJ/921EJ				47		
	UNR921AJ/921BJ				100		

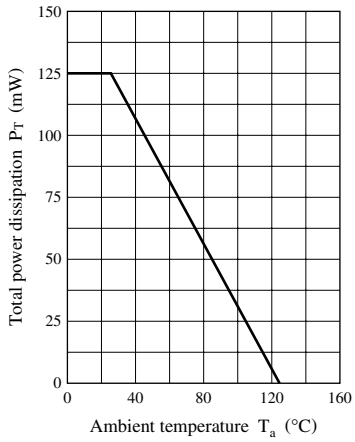
■ Electrical Characteristics (continued) $T_a = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Emitter-base resistance	UNR921CJ	R_2		−30%	47	+30%	kΩ
Rasistance ratio	UNR921MJ	R_1/R_2			0.047		—
	UNR921NJ				0.1		
	UNR9218J/9219J			0.08	0.10	0.12	
	UNR9214J			0.17	0.21	0.25	
	UNR921TJ				0.47		
	UNR921FJ			0.37	0.47	0.57	
	UNR921AJ/921VJ				1.0		
	UNR9211J/9212J/9213J/921LJ			0.8	1.0	1.2	
	UNR921KJ			1.70	2.13	2.60	
	UNR921EJ			1.70	2.14	2.60	
	UNR921DJ			3.7	4.7	5.7	

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

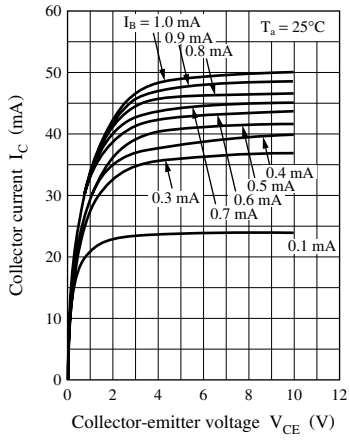
Common characteristics chart

P_T — T_a

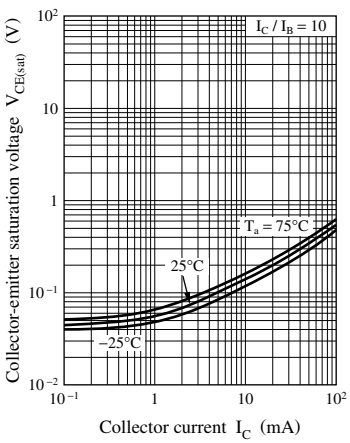


Characteristics charts of UNR9210J

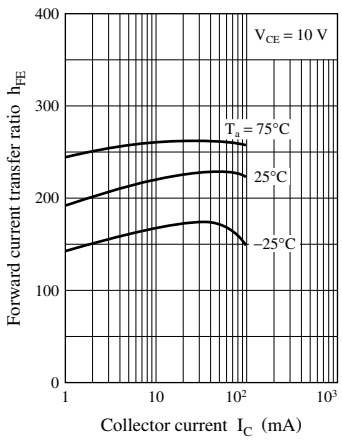
I_C — V_{CE}



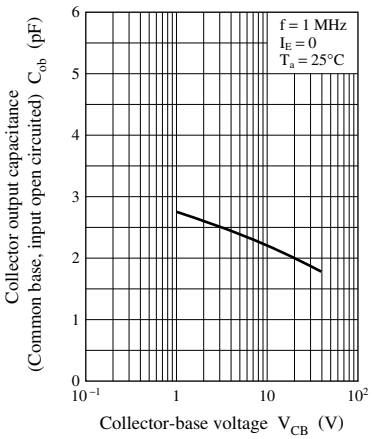
$V_{CE(sat)}$ — I_C



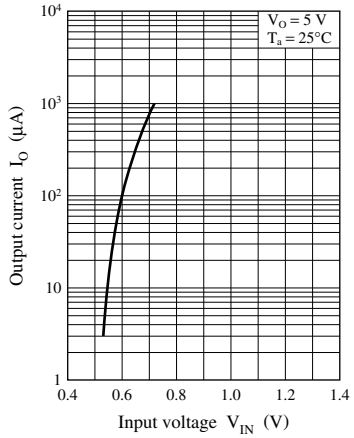
h_{FE} — I_C



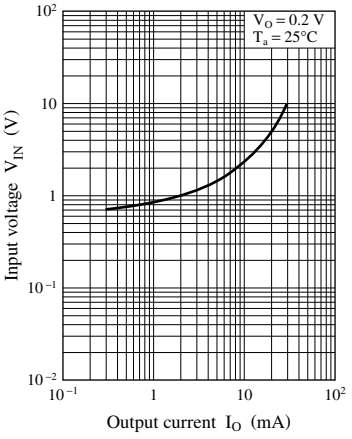
C_{ob} — V_{CB}



I_O — V_{IN}

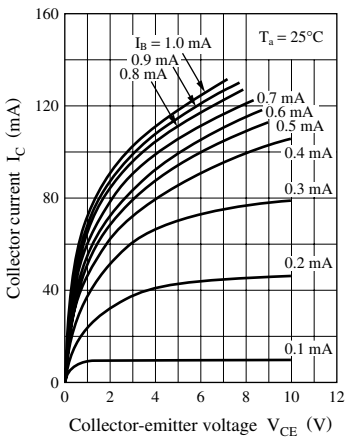


V_{IN} — I_O

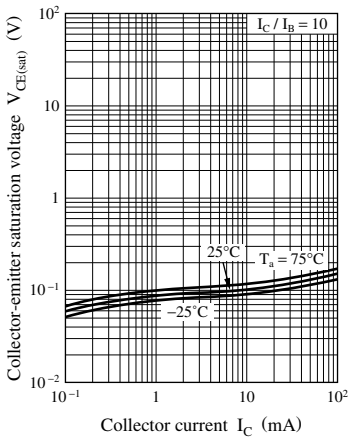


Characteristics charts of UNR9211J

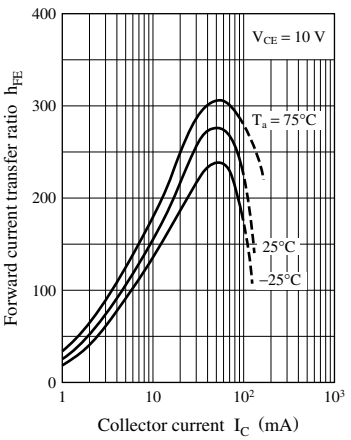
I_C — V_{CE}



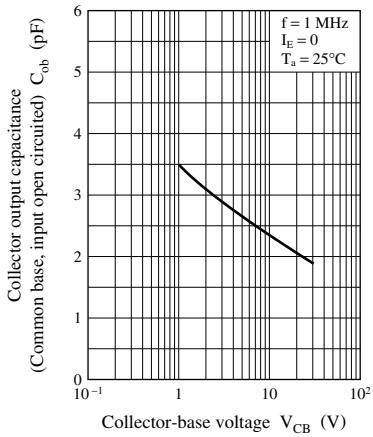
$V_{CE(sat)}$ — I_C



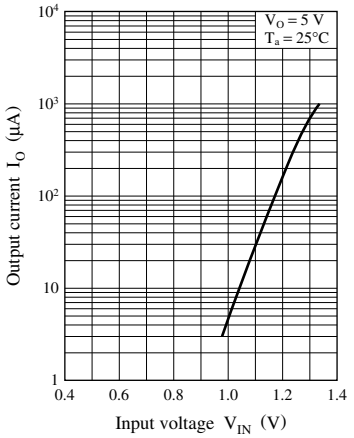
h_{FE} — I_C



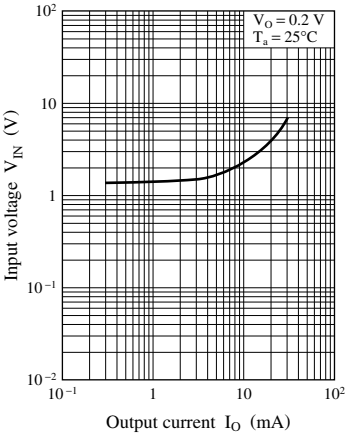
C_{ob} — V_{CB}



I_O — V_{IN}

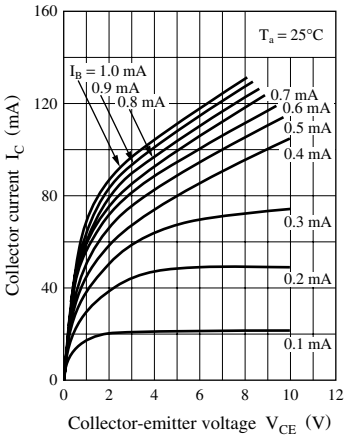


V_{IN} — I_O

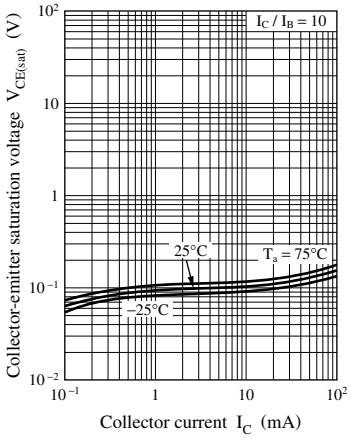


Characteristics charts of UNR9212J

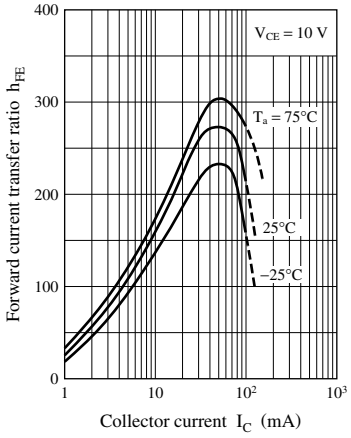
I_C — V_{CE}



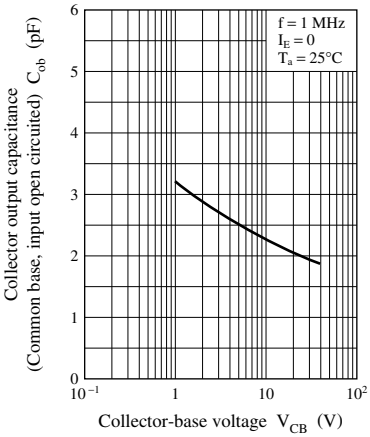
$V_{CE(sat)}$ — I_C



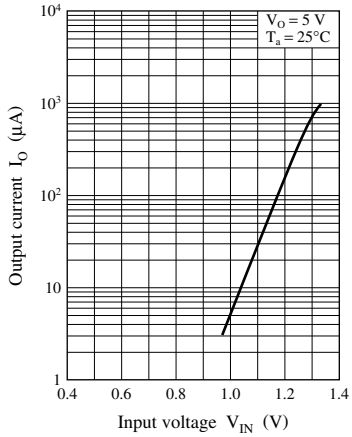
h_{FE} — I_C



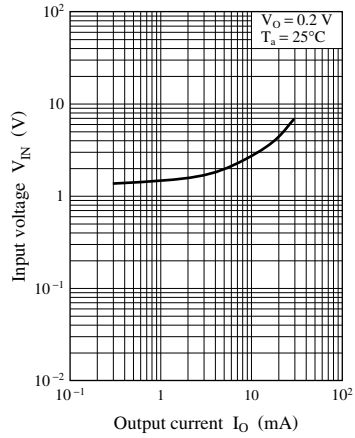
C_{ob} — V_{CB}



I_O — V_{IN}

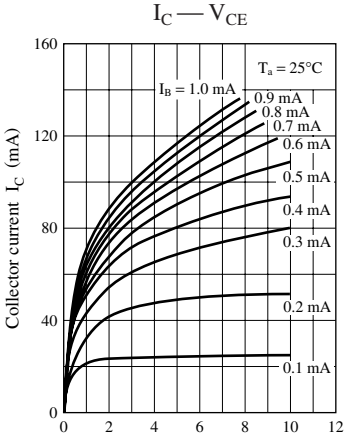


V_{IN} — I_O

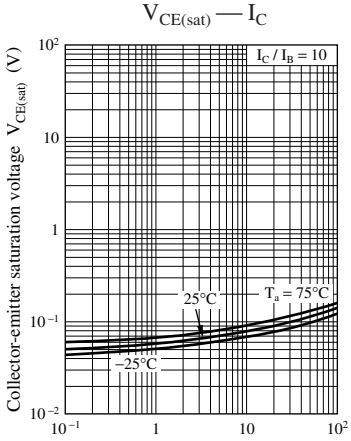


Characteristics charts of UNR9213J

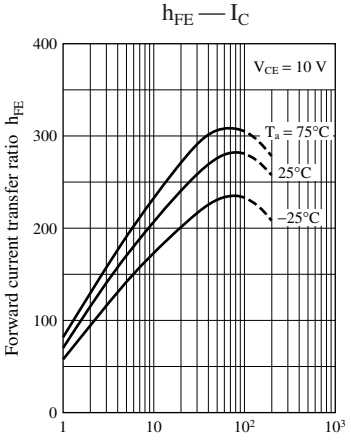
I_C — V_{CE}



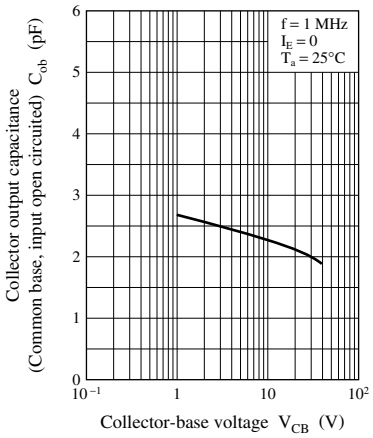
$V_{CE(sat)}$ — I_C



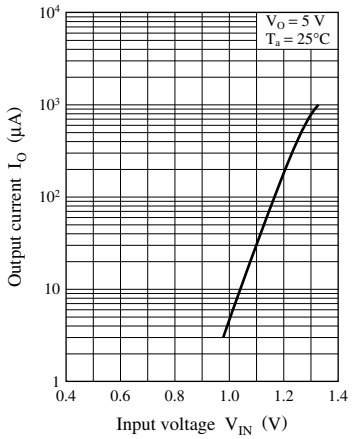
h_{FE} — I_C



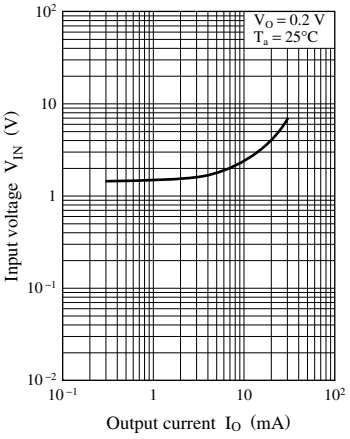
C_{ob} — V_{CB}



I_O — V_{IN}

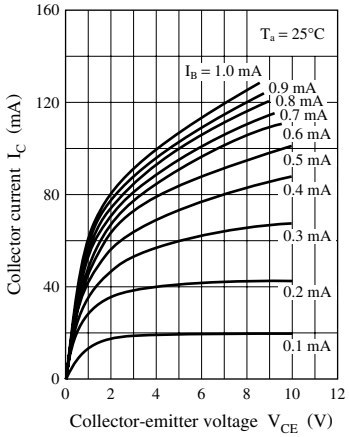


V_{IN} — I_O

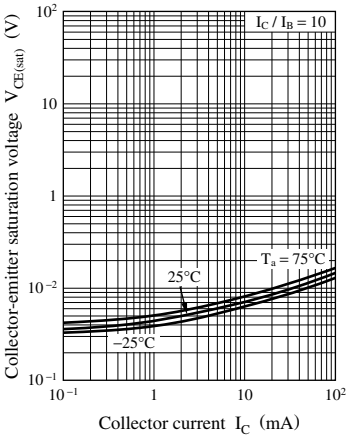


Characteristics charts of UNR9214J

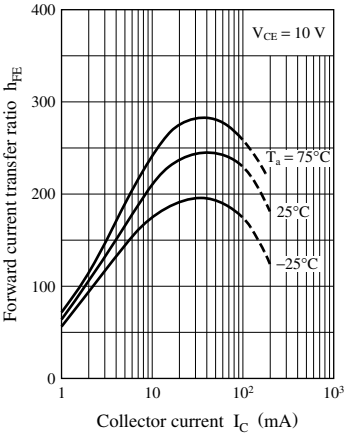
I_C — V_{CE}



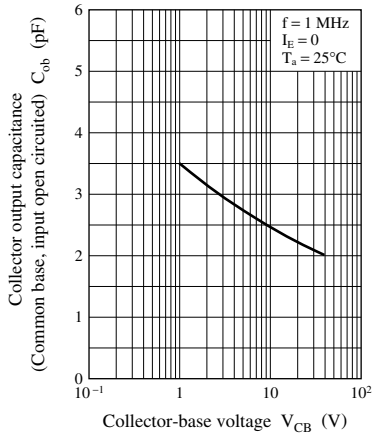
$V_{CE(sat)}$ — I_C



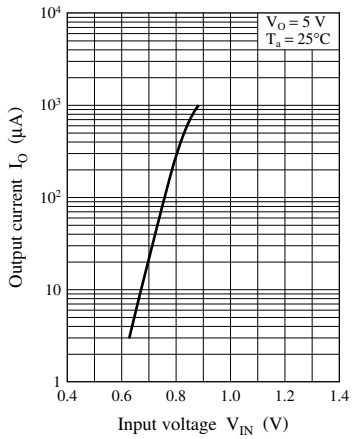
h_{FE} — I_C



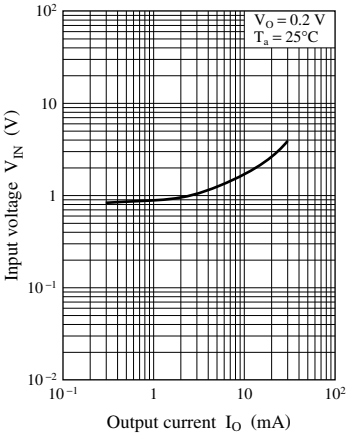
C_{ob} — V_{CB}



I_O — V_{IN}

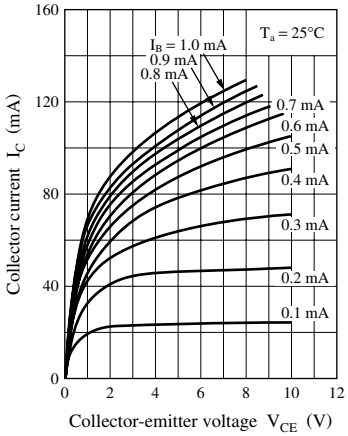


V_{IN} — I_O

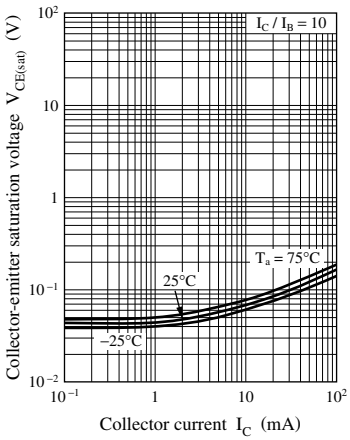


Characteristics charts of UNR9215J

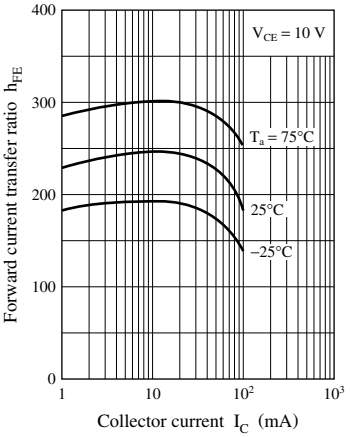
I_C — V_{CE}



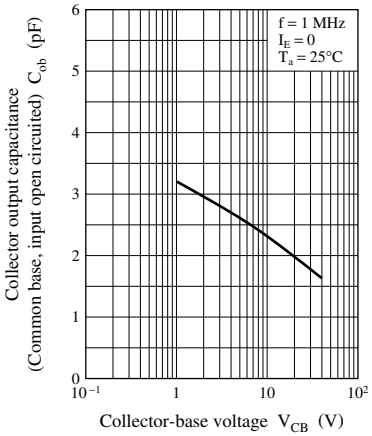
$V_{CE(sat)}$ — I_C



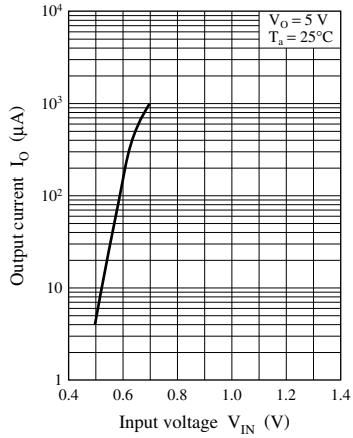
h_{FE} — I_C



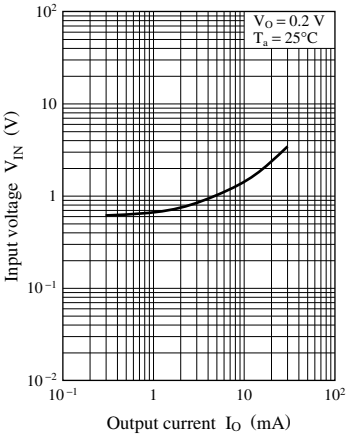
C_{ob} — V_{CB}



I_O — V_{IN}

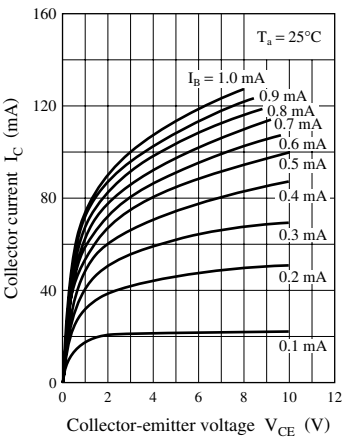


V_{IN} — I_O

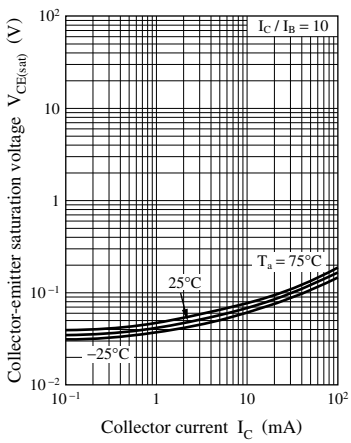


Characteristics charts of UNR9216J

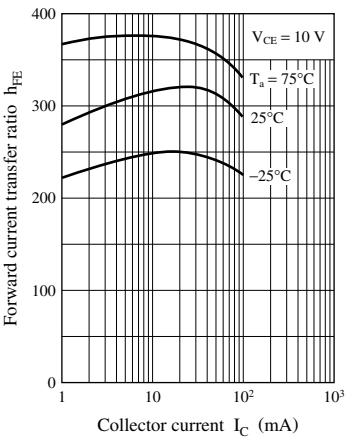
I_C — V_{CE}



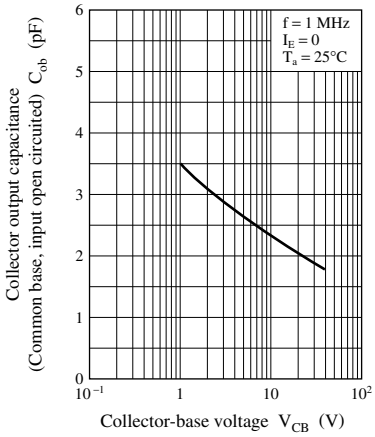
$V_{CE(sat)}$ — I_C



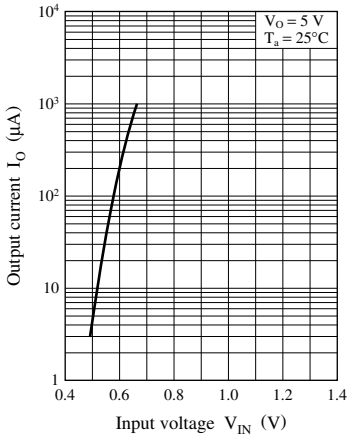
h_{FE} — I_C



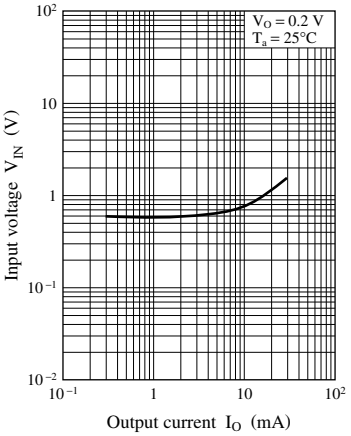
C_{ob} — V_{CB}



I_O — V_{IN}

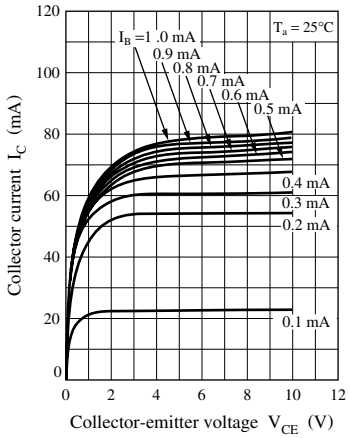


V_{IN} — I_O

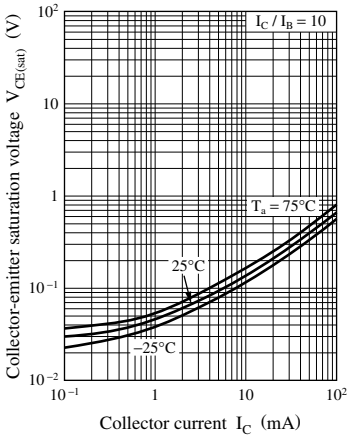


Characteristics charts of UNR9217J

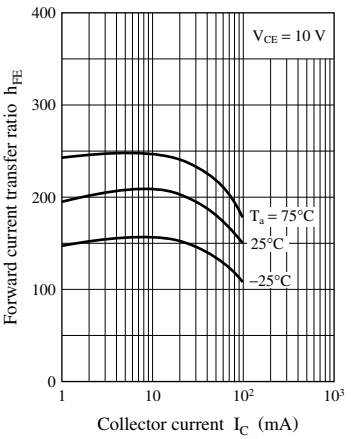
I_C — V_{CE}



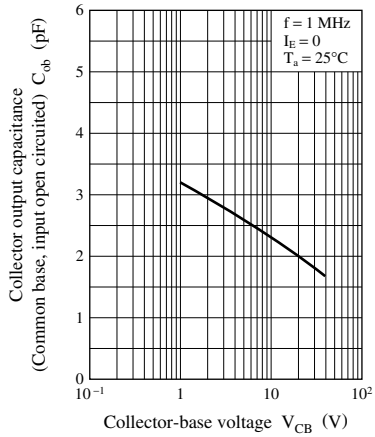
$V_{CE(sat)}$ — I_C



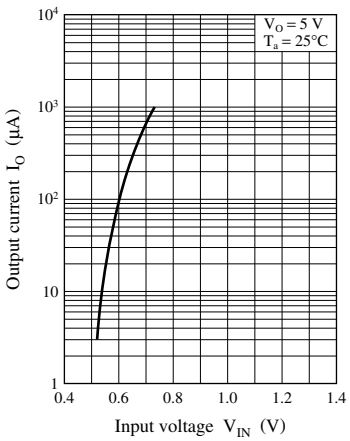
h_{FE} — I_C



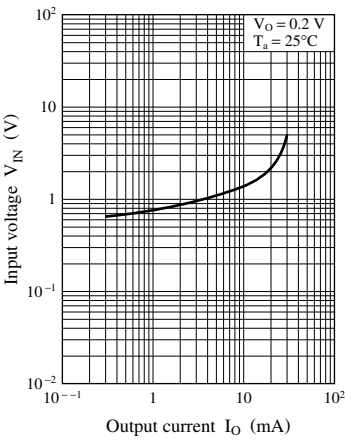
C_{ob} — V_{CB}



I_O — V_{IN}

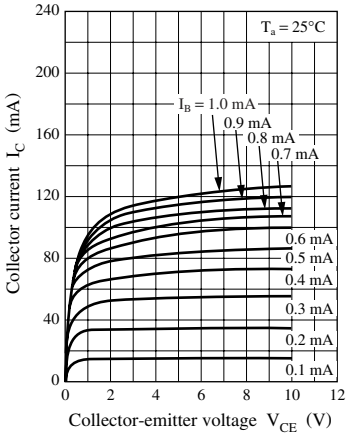


V_{IN} — I_O

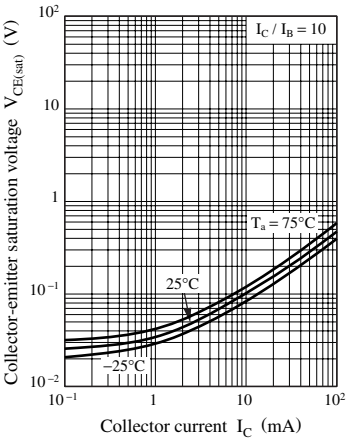


Characteristics charts of UNR9218J

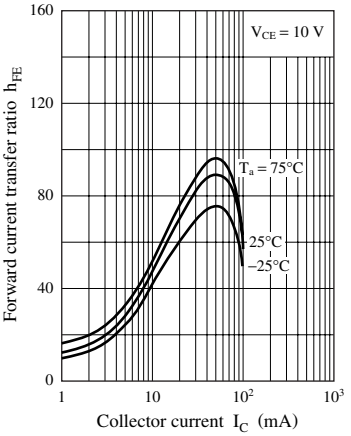
I_C — V_{CE}



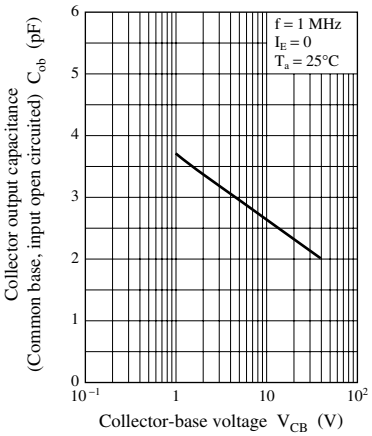
$V_{CE(sat)}$ — I_C



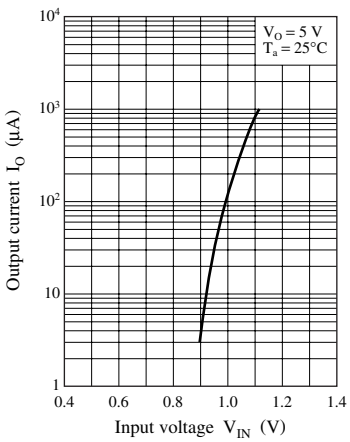
h_{FE} — I_C



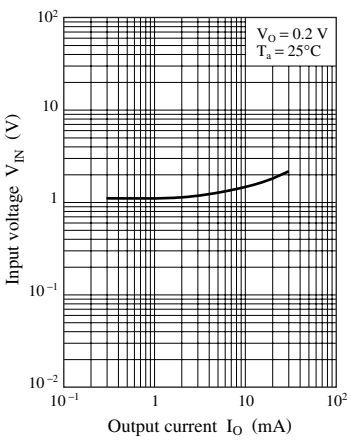
C_{ob} — V_{CB}



I_O — V_{IN}

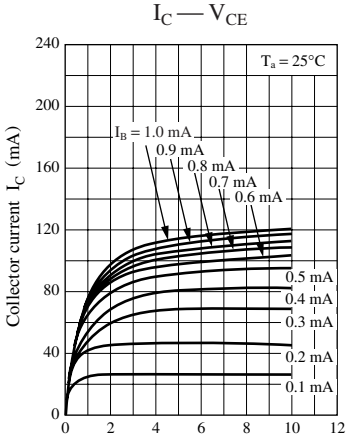


V_{IN} — I_O

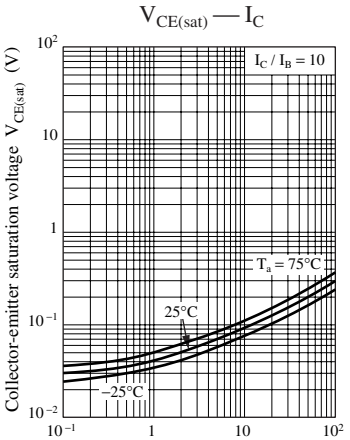


Characteristics charts of UNR9219J

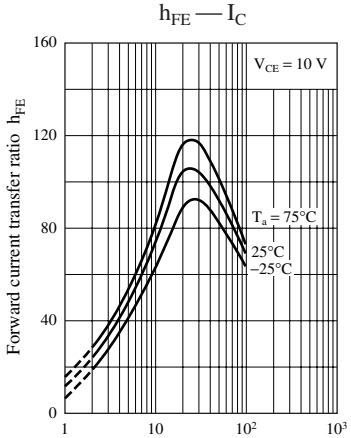
I_C — V_{CE}



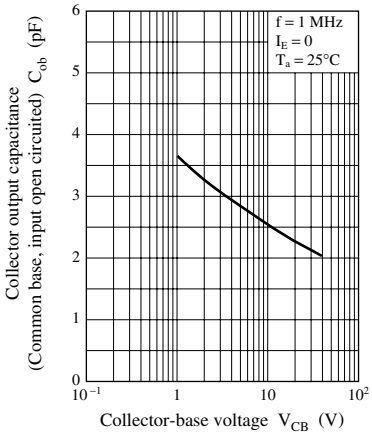
$V_{CE(sat)}$ — I_C



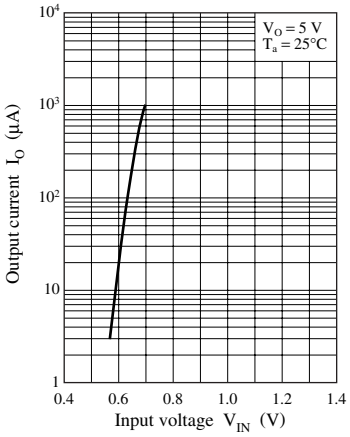
h_{FE} — I_C



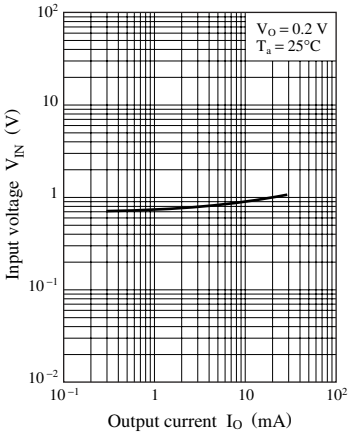
C_{ob} — V_{CB}



I_O — V_{IN}

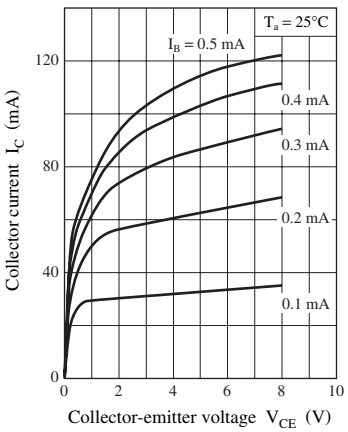


V_{IN} — I_O

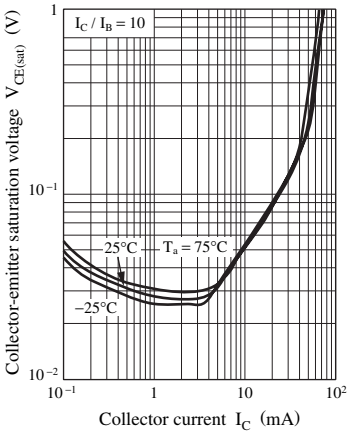


Characteristics charts of UNR921AJ

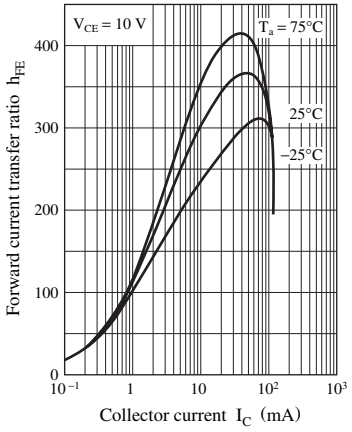
I_C — V_{CE}



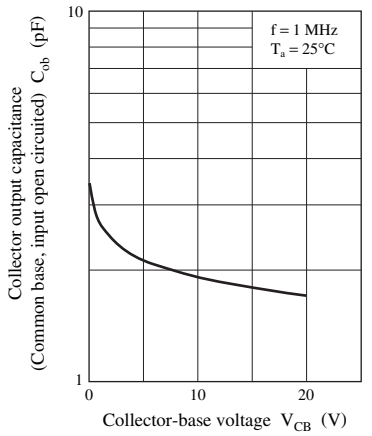
$V_{CE(sat)}$ — I_C



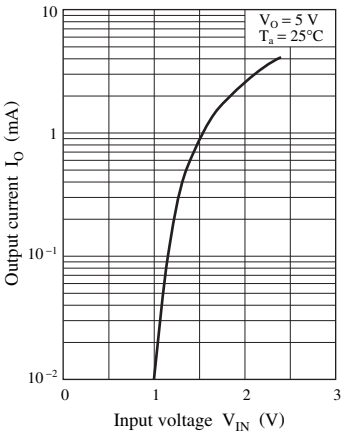
h_{FE} — I_C



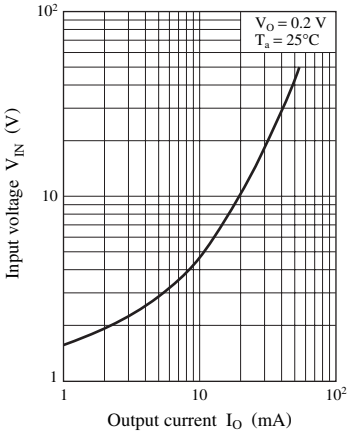
C_{ob} — V_{CB}



I_O — V_{IN}

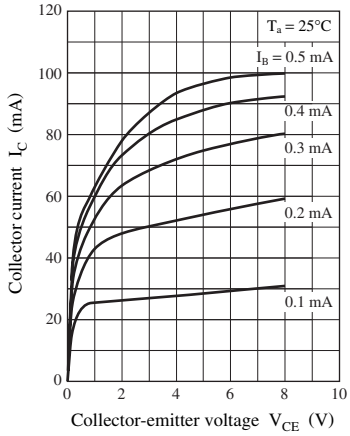


V_{IN} — I_O

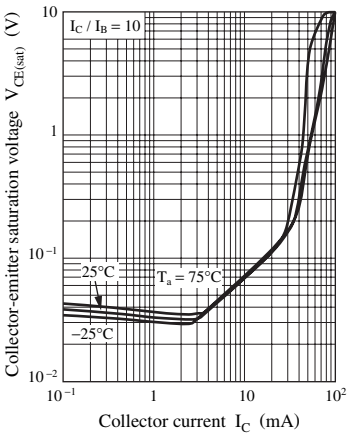


Characteristics charts of UNR921BJ

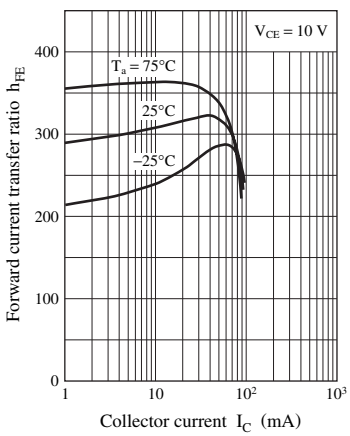
I_C — V_{CE}



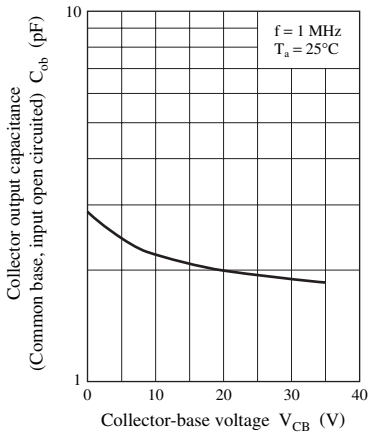
$V_{CE(sat)}$ — I_C



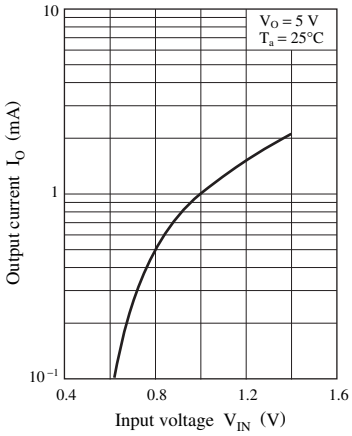
h_{FE} — I_C



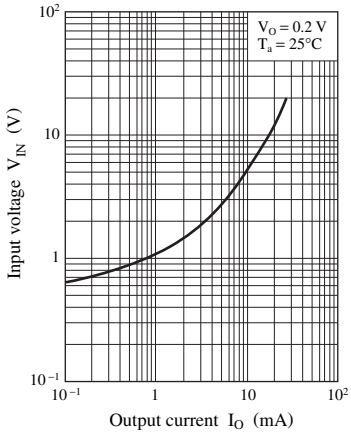
C_{ob} — V_{CB}



I_O — V_{IN}

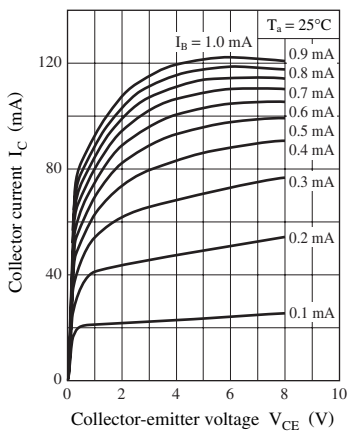


V_{IN} — I_O

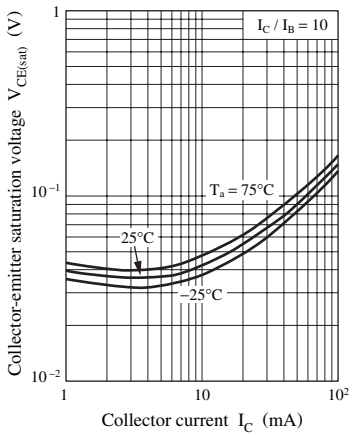


Characteristics charts of UNR921CJ

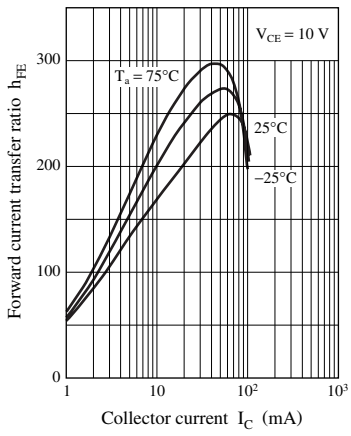
I_C — V_{CE}



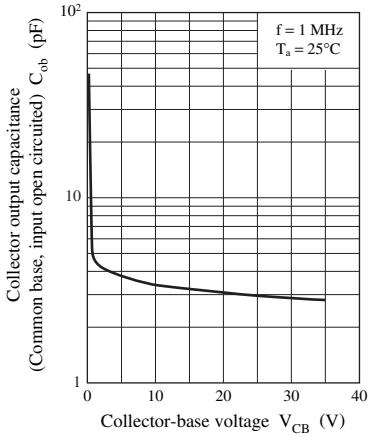
$V_{CE(sat)}$ — I_C



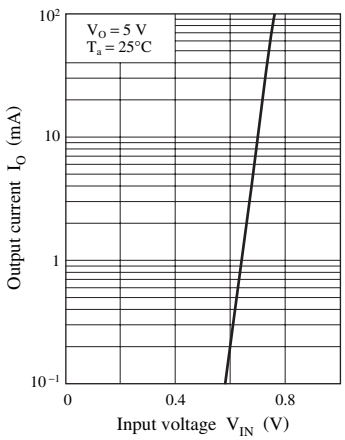
h_{FE} — I_C



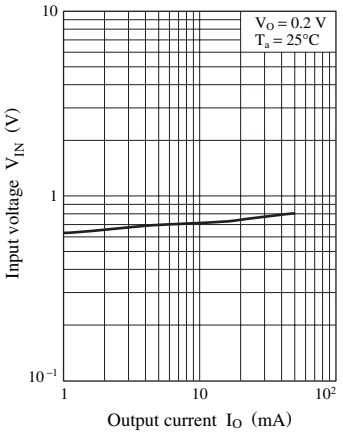
C_{ob} — V_{CB}



I_O — V_{IN}

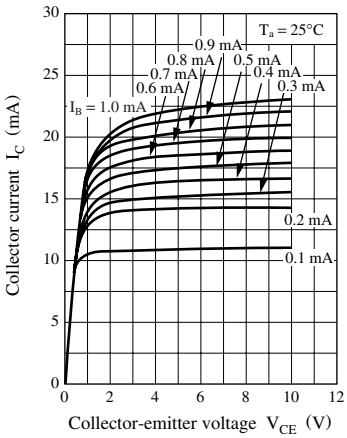


V_{IN} — I_O

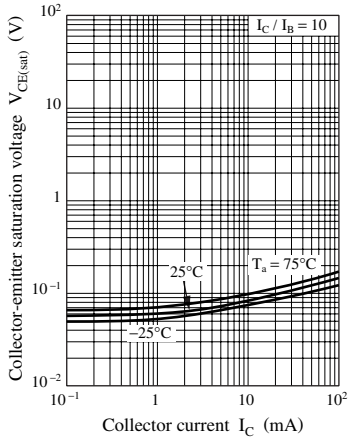


Characteristics charts of UNR921DJ

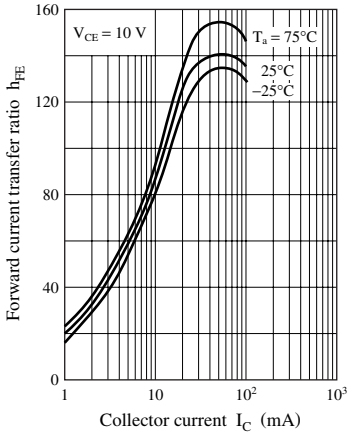
I_C — V_{CE}



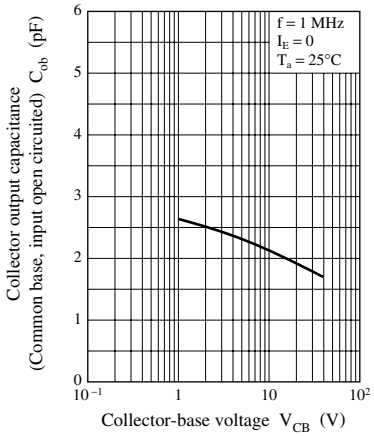
$V_{CE(sat)}$ — I_C



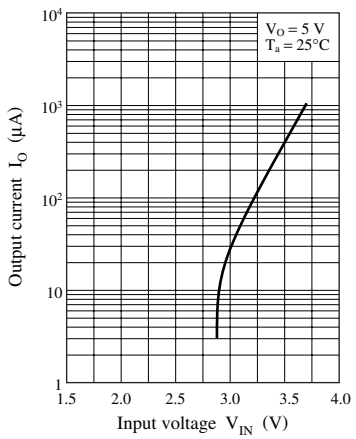
h_{FE} — I_C



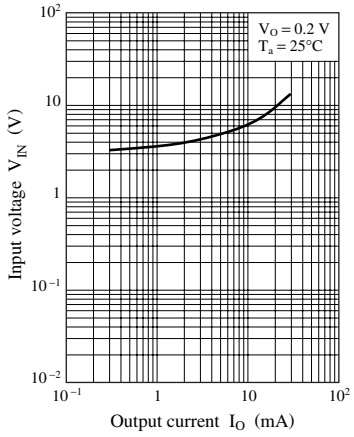
C_{ob} — V_{CB}



I_O — V_{IN}

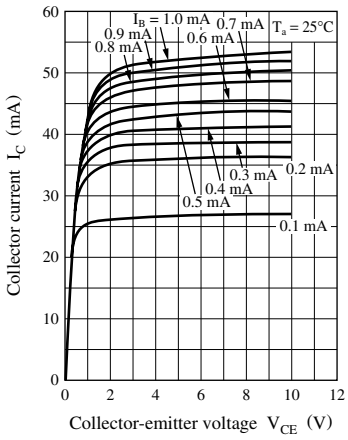


V_{IN} — I_O

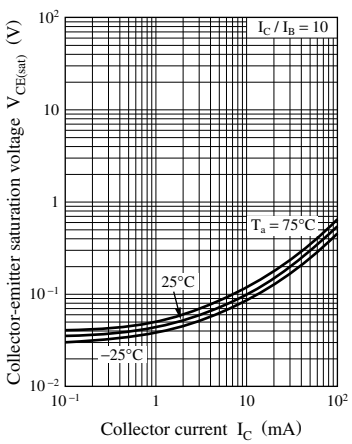


Characteristics charts of UNR921EJ

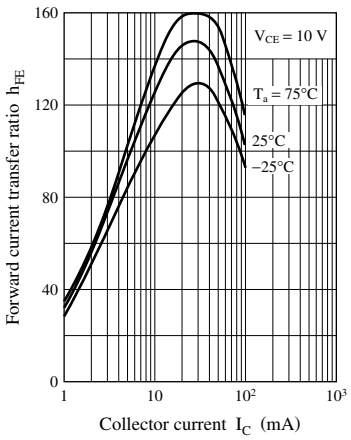
I_C — V_{CE}



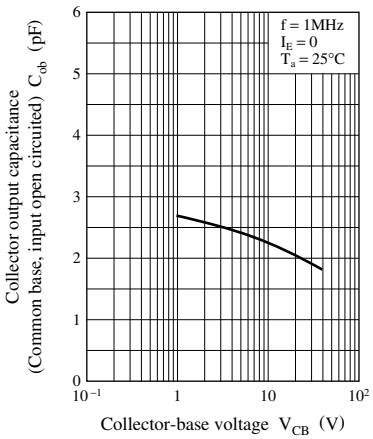
$V_{CE(sat)}$ — I_C



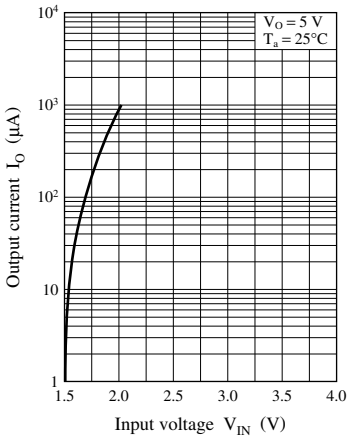
h_{FE} — I_C



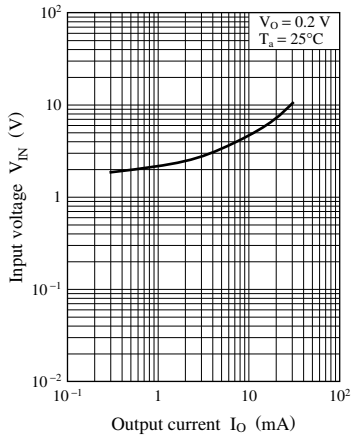
C_{ob} — V_{CB}



I_O — V_{IN}

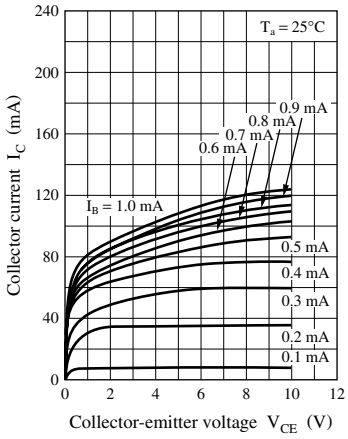


V_{IN} — I_O

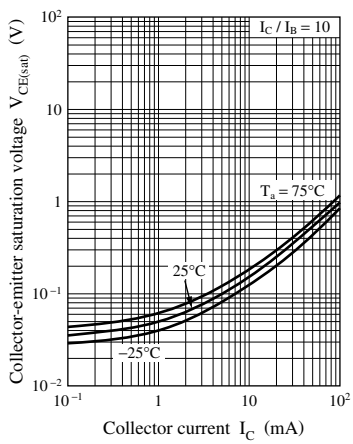


Characteristics charts of UNR921FJ

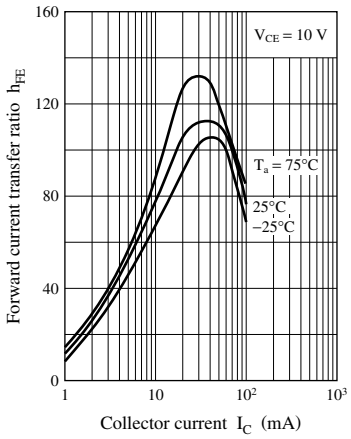
I_C — V_{CE}



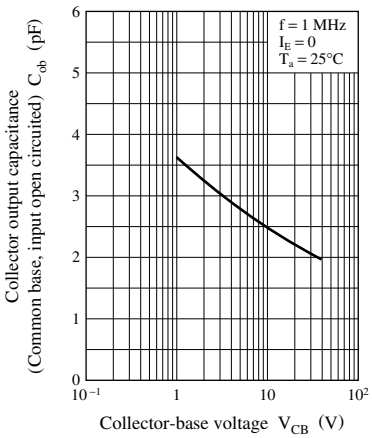
$V_{CE(sat)}$ — I_C



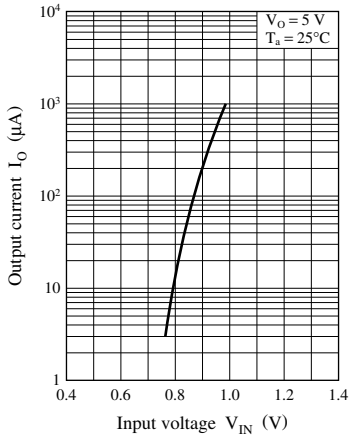
h_{FE} — I_C



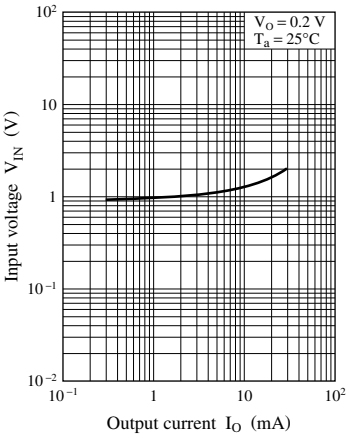
C_{ob} — V_{CB}



I_O — V_{IN}

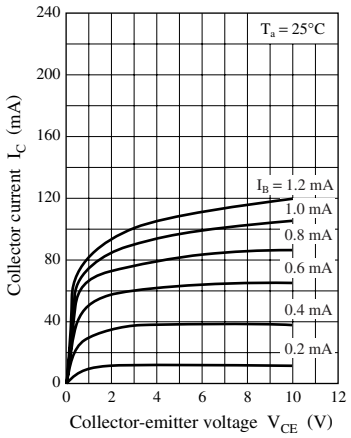


V_{IN} — I_O

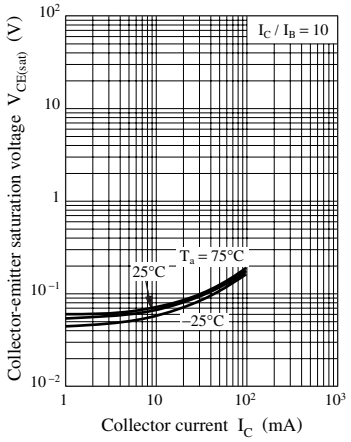


Characteristics charts of UNR921KJ

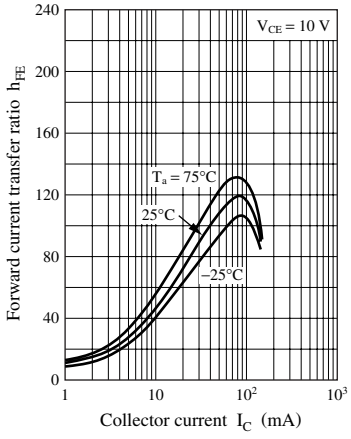
I_C — V_{CE}



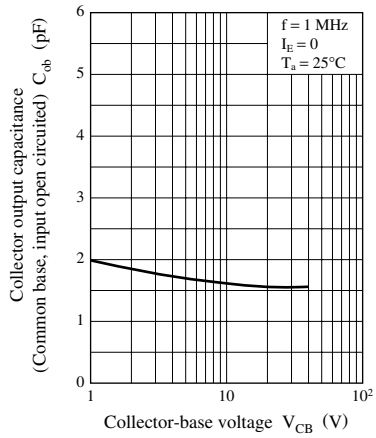
$V_{CE(sat)}$ — I_C



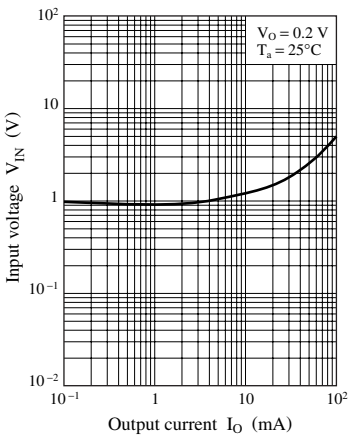
h_{FE} — I_C



C_{ob} — V_{CB}

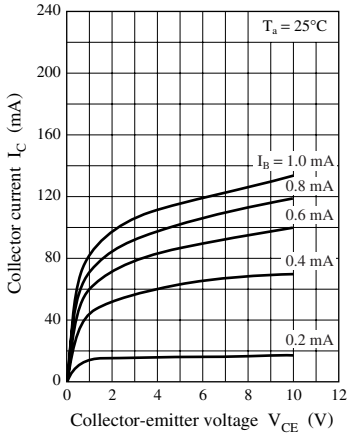


V_{IN} — I_O

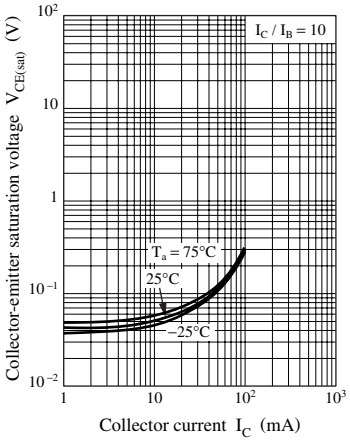


Characteristics charts of UNR921LJ

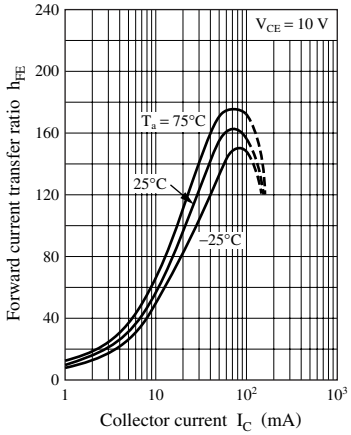
I_C — V_{CE}



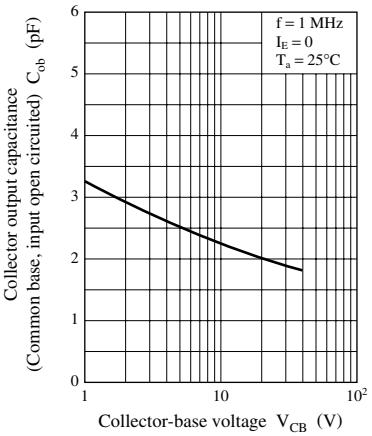
$V_{CE(sat)}$ — I_C



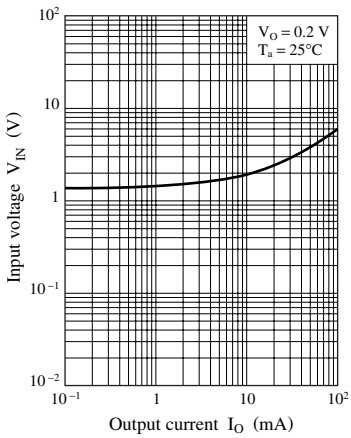
h_{FE} — I_C



C_{ob} — V_{CB}

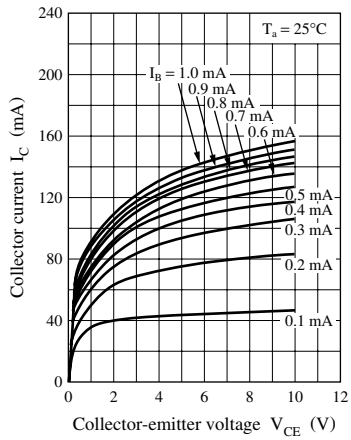


V_{IN} — I_O

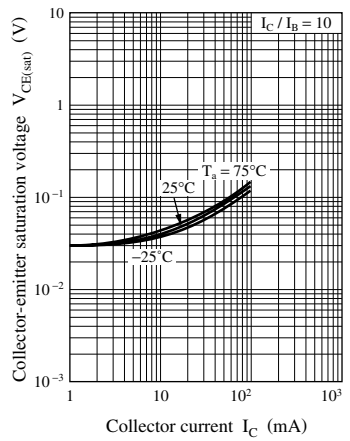


Characteristics charts of UNR921MJ

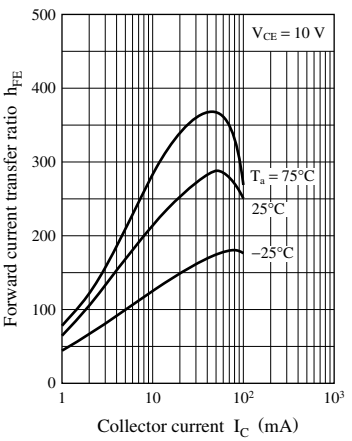
I_C — V_{CE}



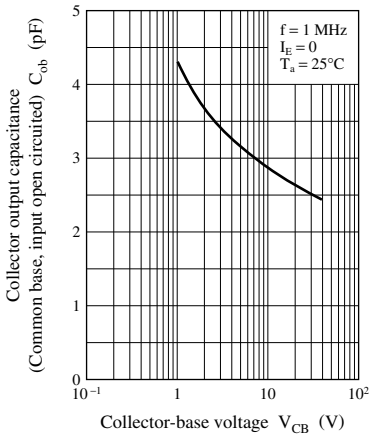
$V_{CE(sat)}$ — I_C



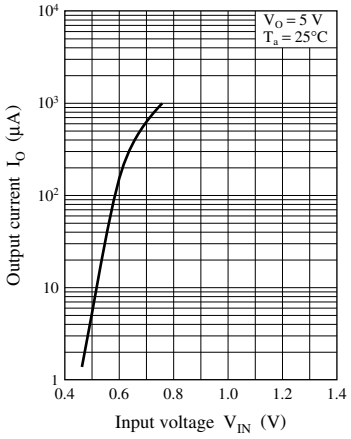
h_{FE} — I_C



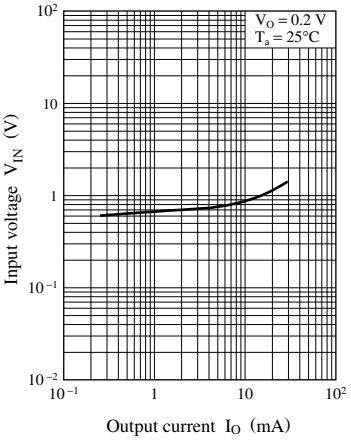
C_{ob} — V_{CB}



I_O — V_{IN}

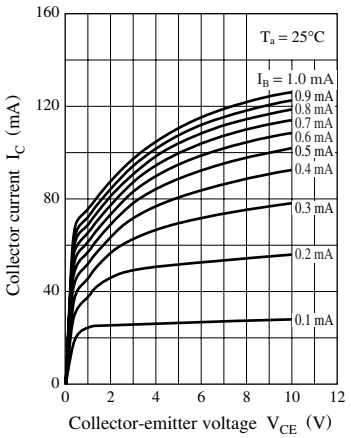


V_{IN} — I_O

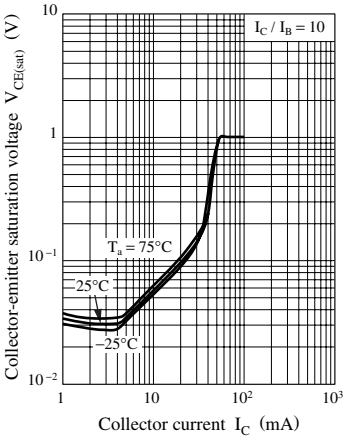


Characteristics charts of UNR921NJ

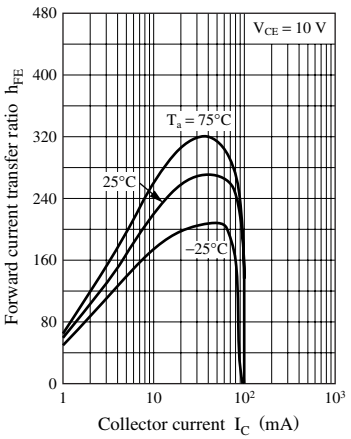
I_C — V_{CE}



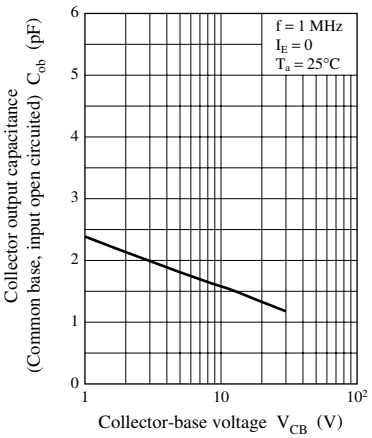
$V_{CE(sat)}$ — I_C



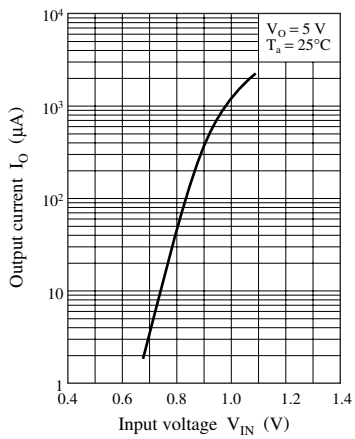
h_{FE} — I_C



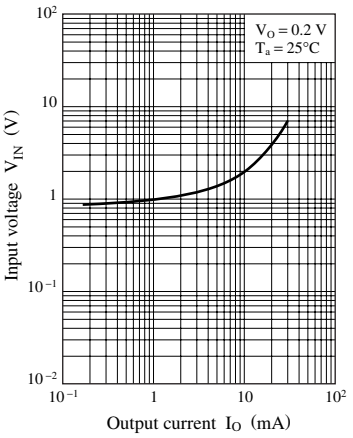
C_{ob} — V_{CB}



I_O — V_{IN}

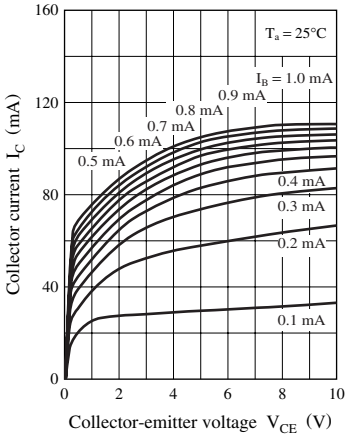


V_{IN} — I_O

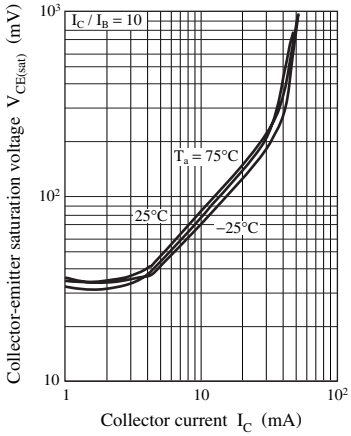


Characteristics charts of UNR921TJ

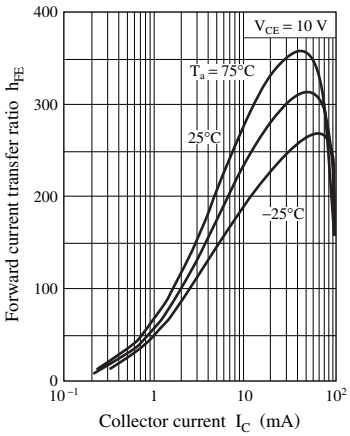
I_C — V_{CE}



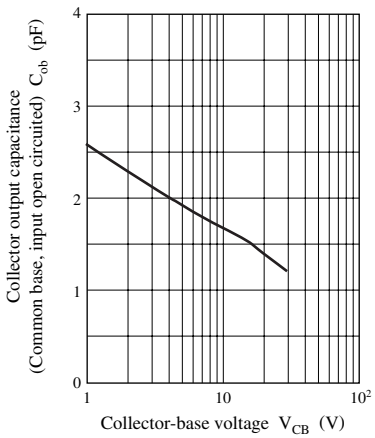
$V_{CE(sat)}$ — I_C



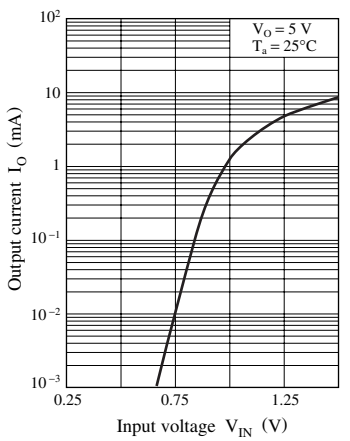
h_{FE} — I_C



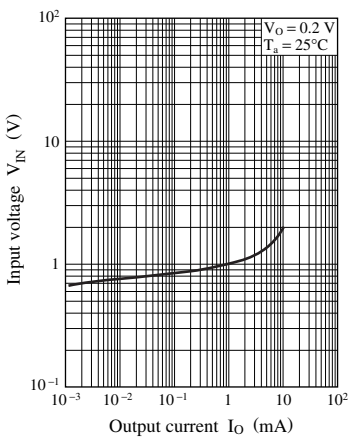
C_{ob} — V_{CB}



I_O — V_{IN}

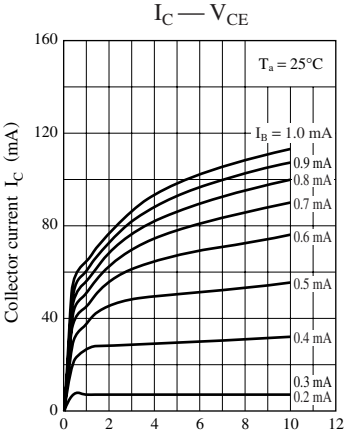


V_{IN} — I_O

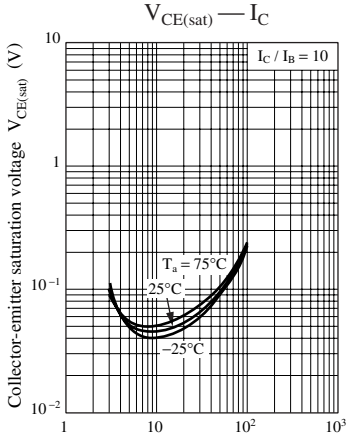


Characteristics charts of UNR921VJ

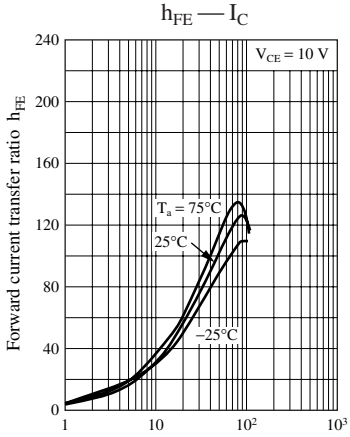
I_C — V_{CE}



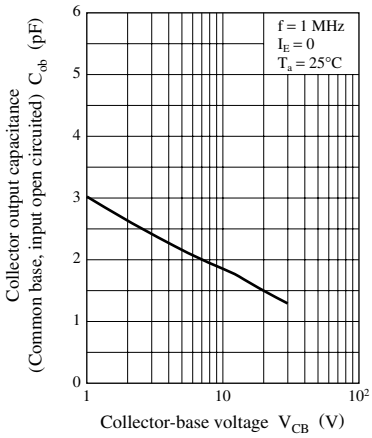
$V_{CE(sat)}$ — I_C



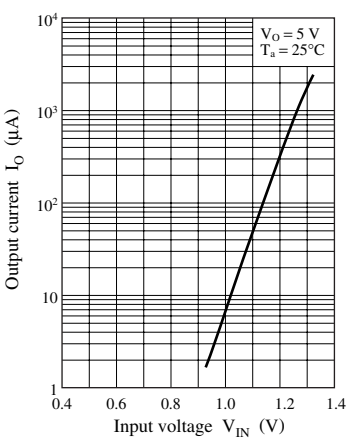
h_{FE} — I_C



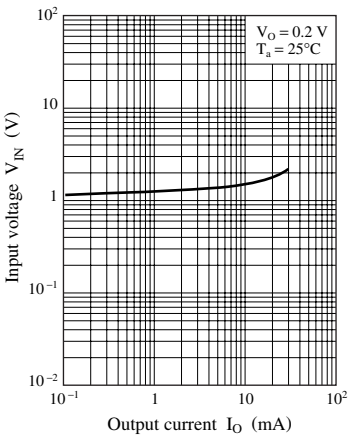
C_{ob} — V_{CB}



I_O — V_{IN}



V_{IN} — I_O



Request for your special attention and precautions in using the technical information and semiconductors described in this material

(1) An export permit needs to be obtained from the competent authorities of the Japanese Government if any of the products or technical information described in this material and controlled under the "Foreign Exchange and Foreign Trade Law" is to be exported or taken out of Japan.

(2) The technical information described in this material is limited to showing representative characteristics and applied circuits examples of the products. It neither warrants non-infringement of intellectual property right or any other rights owned by our company or a third party, nor grants any license.

(3) We are not liable for the infringement of rights owned by a third party arising out of the use of the technical information as described in this material.

(4) The products described in this material are intended to be used for standard applications or general electronic equipment (such as office equipment, communications equipment, measuring instruments and household appliances).
Consult our sales staff in advance for information on the following applications:
- Special applications (such as for airplanes, aerospace, automobiles, traffic control equipment, combustion equipment, life support systems and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
- Any applications other than the standard applications intended.

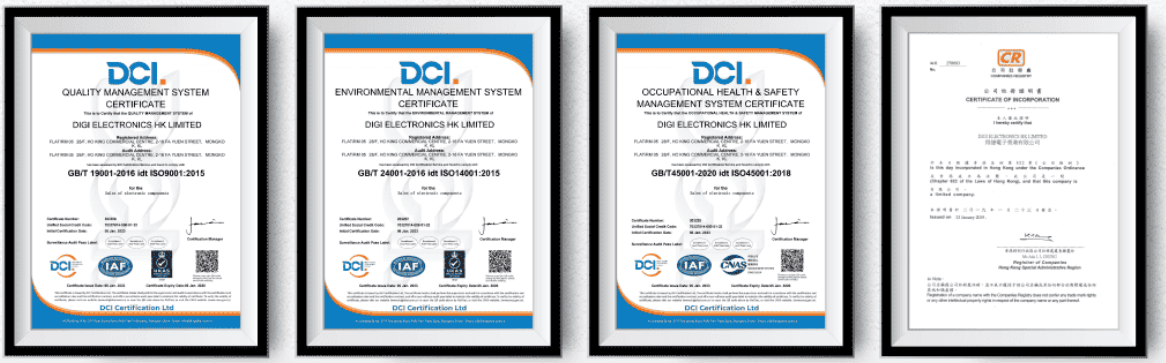
(5) The products and product specifications described in this material are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most up-to-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.

(6) When designing your equipment, comply with the guaranteed values, in particular those of maximum rating, the range of operating power supply voltage, and heat radiation characteristics. Otherwise, we will not be liable for any defect which may arise later in your equipment.
Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.

(7) When using products for which damp-proof packing is required, observe the conditions (including shelf life and amount of time let standing of unsealed items) agreed upon when specification sheets are individually exchanged.

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.